Time		Coherence	Qubit	Material	Host	Date	Reference	Source
57	s	T_1	LD/e	GaAs/AlGaAs	2D	2018-08	1	p3 and Fig. 4a
30	s	T_1	LD/i	Si:P	imp	2017-03	2	Fig. 2b the lowest point
16	s	T_1	LD/i	Si:P	imp	2023-11	3	Tab. I
11	s[a]	T_1	LD/i	Si:P	imp	2023-02	4	p6
10	s	T_1	LD/e	GaAs/AlGaAs	2D	2017-10	5	Fig. 2 the lowest green point
9.8	s	T_1	LD/i	Si:P	imp	2019-05	6	Fig. 2c
9.3	s	T_1	LD/i	Si:P	imp	2018-03	7	p3 and Fig. 1f
9	s	T_1	LD/e	Si/SiO_2	1D	2021-03	8	p3 and Fig. 3a the leftmost blue point
6.5	s	T_1	LD/i	^{28}Si:P	imp	2023-02	9	Fig. 3c
6	s	T_1	LD/i	Si:P	imp	2010-09	10	p2
5	s[b]	T_1	LD/e	Si/SiGe	2D	2019-04	11	p4
4.2	s	T_1	LD/i	Si:P	imp	2019-01	12	p3
3.4	s	T_1	LD/i	^{28}Si:P	imp	2021-01	13	p6 and SFig. 3c
3	s	T_1	LD/i	^{28}Si:P	imp	2016-10	14	p3
3	s	T_1	ST/e	Si/SiGe	2D	2012-01	15	p4
2.8	s	T_1	LD/e	Si/SiGe	2D	2011-04	16	p3 and Fig. 3
2.6	s	T_1	LD/e	Si/SiO_2	2D	2013-06	17	p3
1.8	s	T_1	LD/i	Si:P	imp	2013-06	18	Fig. 3
1.6	s	T_1	LD/e	$^{28}Si/SiO_2$	2D	2022-03	19	p4 and Fig. 3c
1.3	s	T_1	LD/i[c]	^{28}Si:P	imp	2016-10	20	p4
1.3	s	T_1	LD/i	Si:P	imp	2018-11	21	p3 and Fig. 2b
1	s	T_1	LD/e	^{28}Si/SiGe	2D	2020-03	22	p6 and Fig. 4a
1	s	T_1	LD/e	$^{28}Si/SiO_2$	2D	2018-10	23	p2
1	s	T_1	LD/e	GaAs/AlGaAs	2D	2008-01	24	p4 and Fig. 3c the leftmost blue point
0.7	s	T_1	LD/i	Si:P	imp	2012-09	25	p3
0.6	s[d]	T_1	LD/e	Si/SiGe	2D	2009-08	26	Fig. 5
0.5	s[e]	T_1	ST/e	$^{28}Si/SiO_2$	2D	2020-04	27	Fig. 4 the leftmost black point
0.17	s	T_1	LD/e	Si/SiGe	2D	2016-11	28	Fig. 6
0.16	s[f]	T_1	LD/e	Si/SiGe	2D	2019-04	11	Fig. 2
0.15	s[g]	T_1	LD/e	$^{28}Si/SiO_2$	2D	2018-08	29	p2 and p4
0.14	s	T_1	ST/e	Si/SiGe	2D	2012-04	30	Fig. 2d
0.13	s	T_1	LD/e	^{28}Si/SiGe	2D	2019-11	31	p4
90	ms	T_1	LD/e	Si/SiO_2	2D	2020-06	32	Fig. 1c
85	ms	T_1	LD/e	GaAs/AlGaAs	2D	2014-12	33	p2 and Fig. 3
50	ms	T_1	LD/e	Si/SiGe	2D	2018-02	34	p1 and ED Fig. 3b
40	ms	T_1	LD/e	Si/SiO_2	2D	2010-03	35	p4 and Fig. 4 the leftmost red point
34	ms	T_1	ST/e	BLG	2D	2024-01	36	p4 and Fig. 3b
32	ms	T_1	LD/h	Ge/SiGe	2D	2020-08	37	p3
32	ms	T_1	LD/e	^{28}Si/SiGe	2D	2022-12	38	p3
22	ms[h]	T_1	LD/e	Si/SiGe	2D	2022-08	39	p2 and ED Fig. 4b-d
20	ms	T_1	HY/e[i]	^{28}Si/SiGe	2D	2022-03	40	p5
16	ms	T_1	LD/h	Ge/SiGe	2D	2021-03	41	Fig. S5 dot 3
15	ms[j]	T_1	ST/e	$^{28}Si/SiO_2$	2D	2020-04	27	Fig. 4 the rightmost black point
11	ms[k]	T_1	LD/e	$^{28}Si/SiO_2$	2D	2023-08	42	p3
10	ms	T_1	LD/e	Si/SiO_2	1D	2022-03	43	p2 and Fig. 2a
8.4	ms	T_1	LD/h	BLG	2D	2022-05	44	p5 and Fig. 4
5	ms	T_1	LD/i	^{28}Si:B	imp	2020-07	45	p3 and Fig. 3b
5	ms[l]	T_1	ST/e	$^{28}Si/SiO_2$	2D	2021-01	46	p4 and Fig. 1d
4.1	ms	T_1	ST/i	Si:P	imp	2014-06	47	
3.7	ms	T_1	LD/e	GaAs/AlGaAs	2D	2016-07	48	p3 and Fig. 2

TABLE I-1. Spin coherence times (part 1). Superscripts stand for the following. [a]: Dot D3. [b]: No micromagnet. [c]: Qubit defined in the rotating frame. [d]: *(estimated)* Fig. 5 the lowest point. [e]: At 0.04 K. [f]: With micromagnet. [g]: At 0.1 K. [h]: The average over the three qubits. [i]: EO qubit. [j]: At 1.5 K. [k]: At 1 K. [l]: Lifetime of T_- state.

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